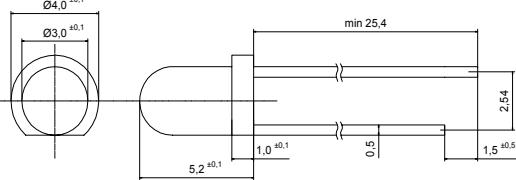


Radiation	Type	Technology	Case
Infrared	DDH	AlGaAs/AlGaAs	3 mm plastic lens

	Description
	 <p>High-power, high-speed infrared LED, compact design in standard 3 mm casing, housing without standoff leads</p>

### Maximum Ratings

$T_{amb} = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
Forward current (DC)		$I_F$	50	mA
Peak forward current	( $t_P \leq 50 \mu\text{s}$ , $t_p/T = 1/2$ )	$I_{FM}$	500	mA
Power dissipation		$P_D$	150	mW
Operating temperature range		$T_{amb}$	-25 to +85	°C
Storage temperature range		$T_{stg}$	-30 to +100	°C
Lead soldering temperature	< 5s, 3.0 mm from case	$T_{sol}$	260	°C

### Optical and Electrical Characteristics

$T_{amb} = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage <sup>1</sup>	$I_F = 50 \text{ mA}$	$V_F$		1.9	2.1	V
Reverse voltage	$I_R = 10 \mu\text{A}$	$V_R$	6			V
Radiant power <sup>1</sup>	$I_F = 50 \text{ mA}$	$\Phi_e$	7	10		mW
Radiant intensity <sup>1</sup>	$I_F = 50 \text{ mA}$	$I_e$	23	32		mW/sr
Peak wavelength	$I_F = 50 \text{ mA}$	$\lambda_p$	690	700	710	nm
Spectral bandwidth at 50%	$I_F = 50 \text{ mA}$	$\Delta\lambda_{0.5}$		33		nm
Viewing angle	$I_F = 50 \text{ mA}$	$\varphi$		15		deg.
Switching time	$I_F = 50 \text{ mA}$	$t_r, t_f$		20/25		ns

<sup>1</sup>for information only

Note: All measurements carried out on *EPIGAP* equipment

We reserve the right to make changes to improve technical design and may do so without further notice.  
Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.

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